

EAST - [10691400.wsp:1]

File View Edit Tools Window Help

Drafts
Pending
Active
L1: (6) oxygen-free near silicon near carbide or oxygen near free near silicon near carbide
L2: (1) 1 and tetramethylsilane
L3: (6) 1 and (tetramethylsilane Torr plasma)
L4: (36) oxygen-free with silicon adj carbide or oxygen near free near silicon near carbide
L5: (0) ("4andtetramethylsilane").PH.
L6: (3) 4 and tetramethylsilane
Filed
Saved
Favorites
Tagged (0)
UDC
Queue
Trash

Section: File Browse Previous Clear
File: US-PGPUB:USPAT:EPG:JPG
Default operation: OR
Highlight all full names and all
oxygen-free with silicon adj carbide or oxygen near free near silicon near carbide

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BRStom ISAR form Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050009320 A1	20050113	13	Method of forming silicon carbide films	438/624	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040161535 A1	20040819	16	Method of forming silicon carbide films	427/249.15	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040137756 A1	20040715	16	METHOD OF IMPROVING STABILITY IN LOW K BARRIER LAYERS	438/778	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040115876 A1	20040617	30	Method of manufacturing silicon carbide film	438/200	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040101625 A1	20040527	15	Nitrogen passivation of interface states in SiO2/SiC structures	427/378	257/E21.267; 257/E21.269
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040067308 A1	20040408	12	Two-layer film for next generation damascene barrier application with good oxidation resistance	427/249.15	257/E21.266; 257/E21.579; 427/569
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20030194496 A1	20031016	9	Methods for depositing dielectric material	427/255.28	427/372.2; 427/569
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030139035 A1	20030724	12	Low dielectric (low k) barrier films with oxygen doping by plasma-enhanced chemical vapor deposition (pecvd)	438/643	257/E21.261; 257/E21.277; 257/E21.579
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030129827 A1	20030710	18	Method of depositing dielectric materials in damascene applications	438/629	257/E21.261; 257/E21.277; 257/E21.579
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030024902 A1	20030206	14	Method of plasma etching low-k dielectric materials	216/87	257/E21.252; 257/E21.256; 257/E21.579
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20010022034 A1	20010920	10	Calibrating body	33/702	33/502